

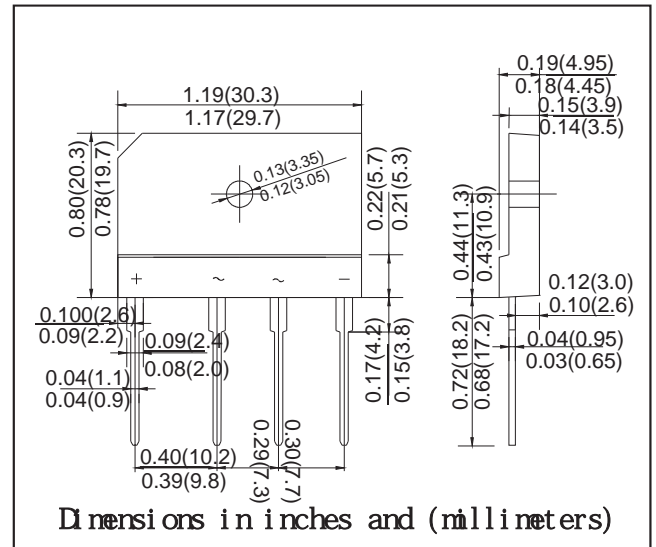
KBJ SILICON BRIDGE RECTIFIER REVERSE VOLTAGE: 50 --- 1000V CURRENT: 10.0A

FEATURES

- "Rating to 1000V PRV
- "Surge overload rating to 200 Amperes peak Ideal for printed circuit board
- "Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- "Lead solderable per MIL-STD-202 method 208

MECHANICAL DATA

- "Polarity: Symbols molded on body
- "Weight: 0.23 ounces, 6.6 grams
- "Mounting position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted) Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

Parameter		KBJ 10A	KBJ 10B	KBJ 10D	KBJ 10G	KBJ 10J	KBJ 10K	KBJ 10M	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=110^\circ\text{C}$	$I_{F(AV)}$	10.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	200.0							A
Maximum instantaneous forward voltage at 5.0 A	V_F	1.1							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	I_R	5.0 0.5							A mA
Typical junction capacitance per element	C_J	55							pF
Typical thermal resistance	R_{JC}	1.4							$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J	- 55 ---- + 150							$^\circ\text{C}$
Storage temperature range	T_{STG}	- 55 ---- + 150							$^\circ\text{C}$

NOTES: 1. Measured at 1.0mA applied reverse voltage of 4.0V DC

2. Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

FIG.1 – PEAK FORWARD SURGE CURRENT

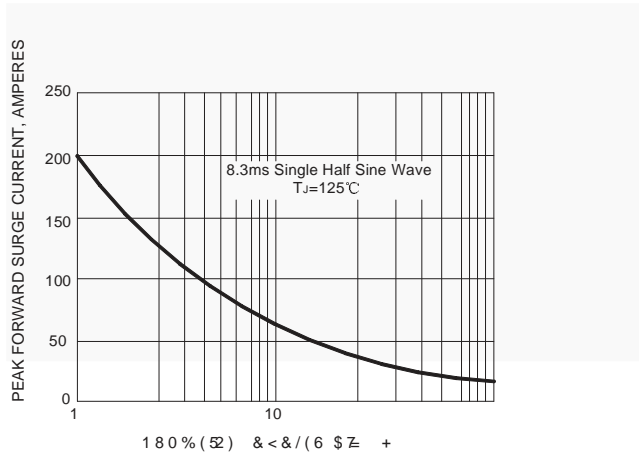


FIG.2 – FORWARD DERATING CURVE

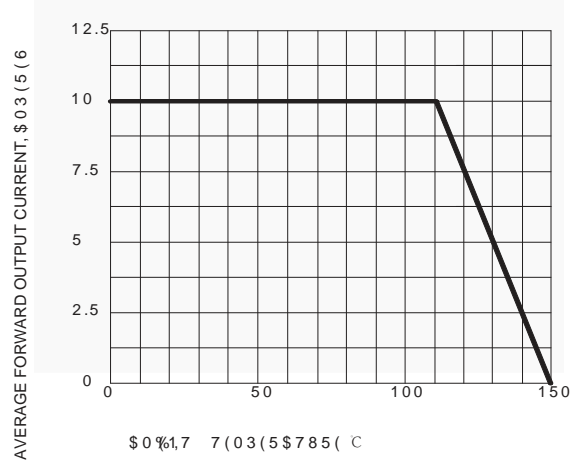


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

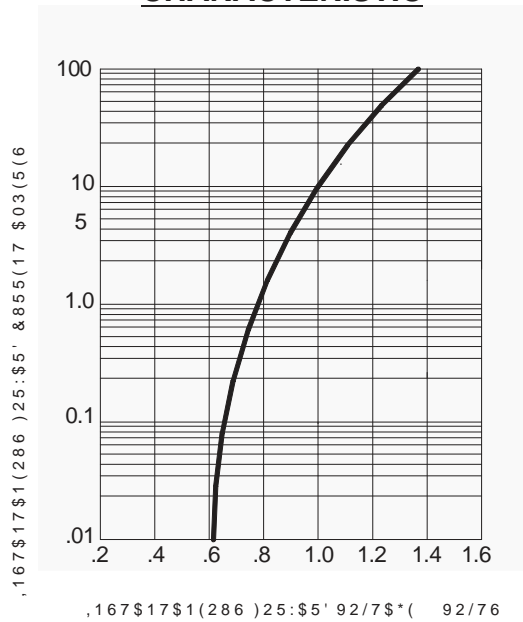


FIG.4 -- TYPICAL JUNCTION CAPACITANCE

